



**CHENMKO ENTERPRISE CO.,LTD**

*Halogens free devices*

**SURFACE MOUNT  
Dual Silicon Transistor**

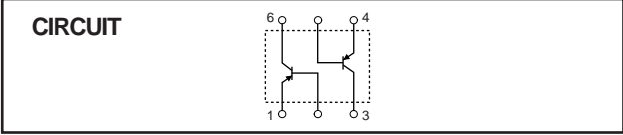
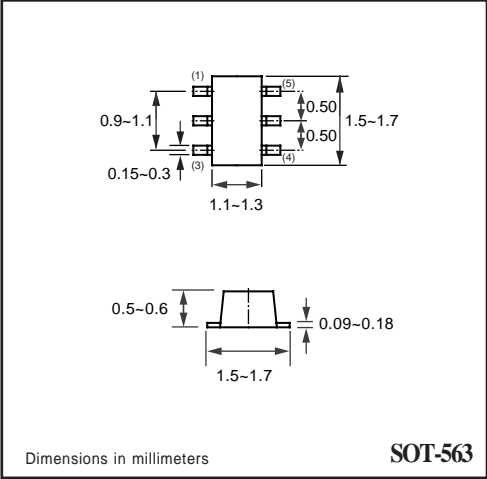
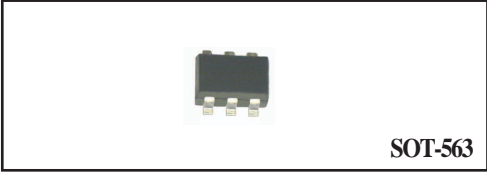
VOLTAGE 12 Volts CURRENT 0.5 Ampere

**CHEMT18GP**

**APPLICATION**  
\* Small Signal Amplifier .

**FEATURE**  
\* Small surface mounting type. (SOT-563)  
\* Low saturation voltage  $V_{CE(sat)} = -0.25V(\text{max.})(I_c=200mA)$   
\* Low cob. Cob=6.5pF(Typ.)  
\*  $P_c = 150mW$  (Total), 120mW per element must not be exceeded.  
\* High saturation current capability.  
\* Two the 2SA2018 in one package.  
\* PNP Silicon Transistor

**MARKING**  
\* T8



**2SA2018 LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CB0</sub>	Collector-base voltage		-	-15	V
V <sub>CE0</sub>	Collector-emitter voltage		-	-12	V
V <sub>EB0</sub>	Emitter-base voltage		-	-6	V
I <sub>C</sub>	DC Output current		-	-500	mA
I <sub>CP</sub>		NOTE.1	-	-1000	
P <sub>c</sub>	power dissipation	NOTE.2	-	150	mW
T <sub>STG</sub>	Storage temperature		-55	+150	°C
T <sub>J</sub>	Junction temperature		-	150	°C

**Note**

1. Single Pulse Pw=1ms
2. 120mW per element must not be exceeded  
Each terminal mounted on a recommended land.

## RATING CHARACTERISTIC CURVES ( CHEMT18GP )

### 2SA2018 CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$BV_{CEO}$	Collector-emitter breakdown voltage	$I_c = -1\text{mA}$	-12	–	–	V
$BV_{CBO}$	Collector-base breakdown voltage	$I_c = -10\text{uA}$	-15	–	–	V
$BV_{EBO}$	Emitter-base breakdown voltage	$I_E = -10\text{uA}$	-6	–	–	V
$I_{CBO}$	Collector cut-off current	$V_{CB} = -15\text{V}$	–	–	-100	nA
$I_{EBO}$	Emitter cut-off current	$V_{EB} = -6\text{V}$	–	–	-100	nA
$h_{FE}$	DC current gain	$V_{CE} = -2\text{V}, I_c = -10\text{mA}$	270	–	680	–
$V_{CE(sat)}$	Collector-emitter saturation voltage	$I_c = -200\text{mA}, I_B = -10\text{mA}$	–	-100	-250	mV
$C_{ob}$	Collector output capacitance	$V_{CB} = -10\text{V}, I_E = 0\text{mA}, f = 1\text{MHz}$	–	6.5	–	pF
$f_T$	Transition frequency	$V_{CE} = -2\text{V}, I_E = 10\text{mA}, f = 100\text{MHz}$	–	260	–	MHz

#### Note

1. Pulse test:  $t_p \leq 300\text{uS}$ ;  $\delta \leq 0.02$ .

## RATING CHARACTERISTIC CURVES ( CHEMT18GP )

### 2SA2018 Typical Electrical Characteristics

Fig.1 Ground emitter propagation characteristics

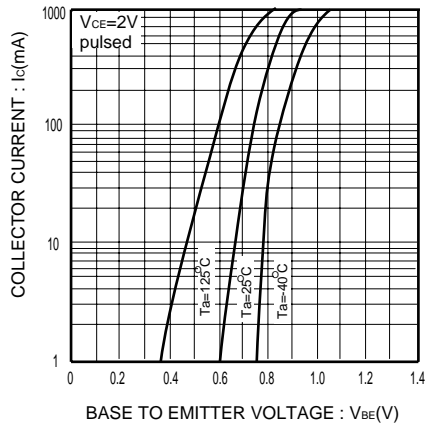


Fig.2 DC current gain vs. collector current

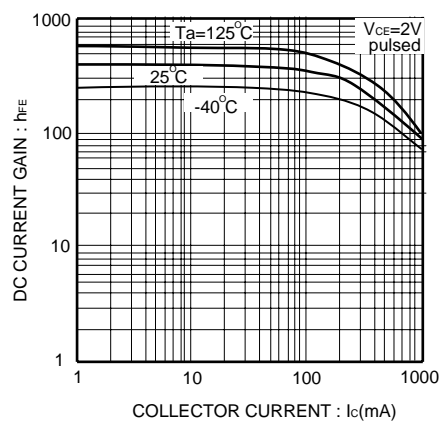


Fig.3 Collector-emitter saturation voltage vs. collector current ( I )

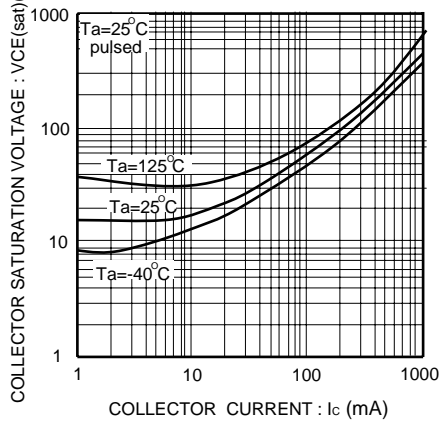
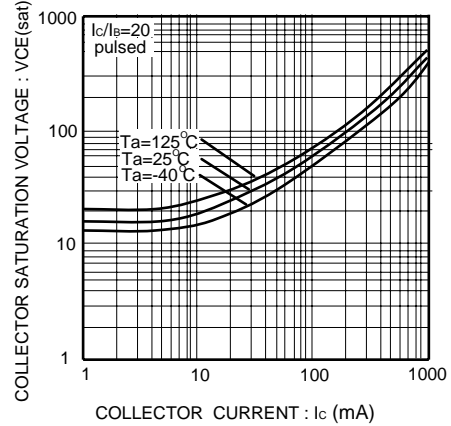


Fig.4 Collector-emitter saturation voltage vs. collector current ( II )



## RATING CHARACTERISTIC CURVES ( CHEMT18GP )

### 2SA2018 Typical Electrical Characteristics

Fig.5 Base-emitter saturation voltage vs. collector current

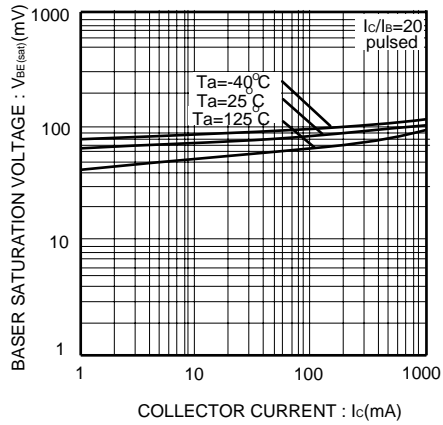


Fig.6 Gain bandwidth product vs. collector current

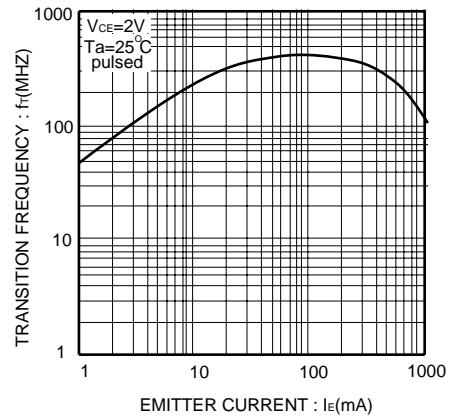


Fig.7 Collector output capacitance vs. collector-base voltage  
Emitter input capacitance vs. emitter-base voltage

